

FIG. 1

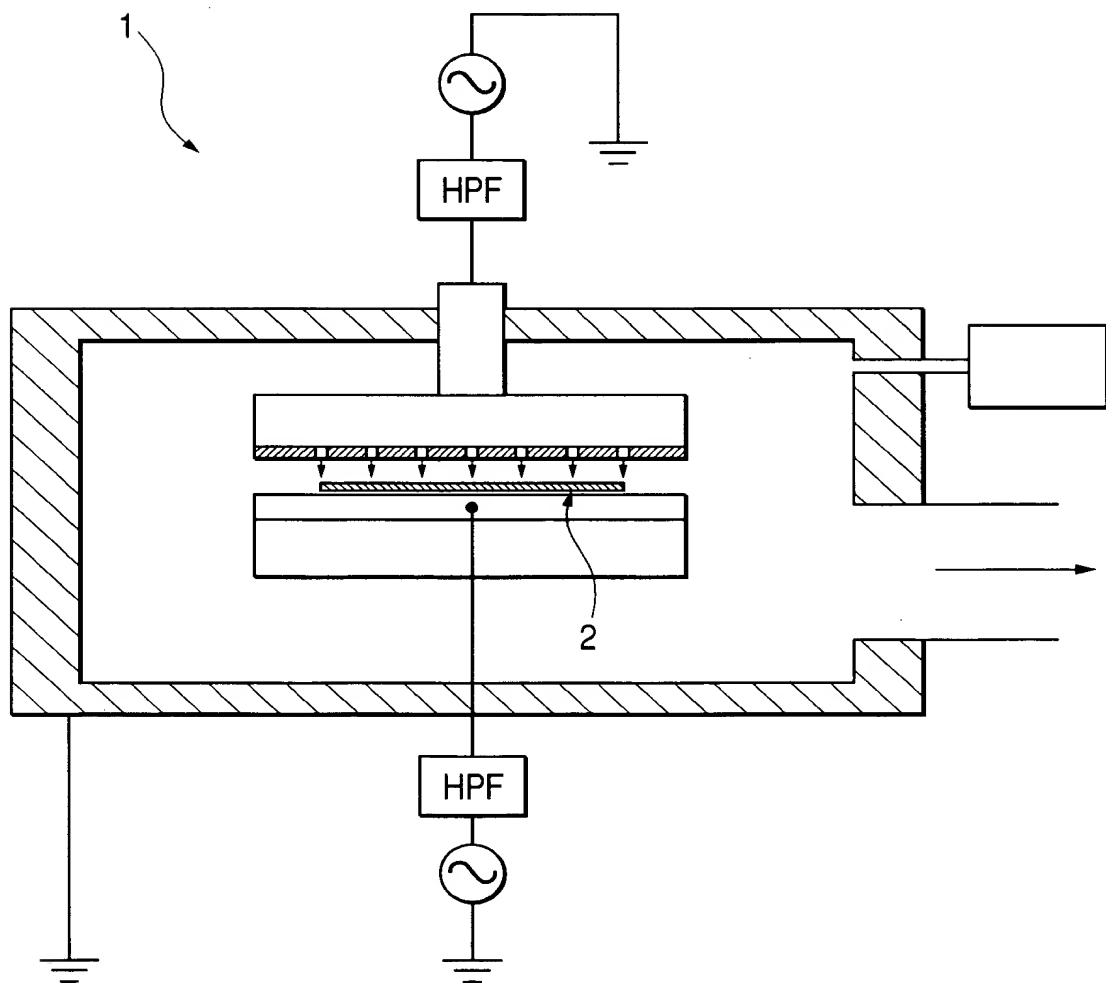


Fig. 1 is a cross-sectional view of a semiconductor device. It shows a substrate 2S(2) at the bottom, a semiconductor layer 3a in the middle, and a gate electrode 4a at the top. The gate electrode 4a is divided into four vertical segments, each with a diagonal hatching pattern. The semiconductor layer 3a is a large rectangular region with diagonal hatching. The substrate 2S(2) is a thin layer at the bottom with a diagonal hatching pattern.

FIG. 3

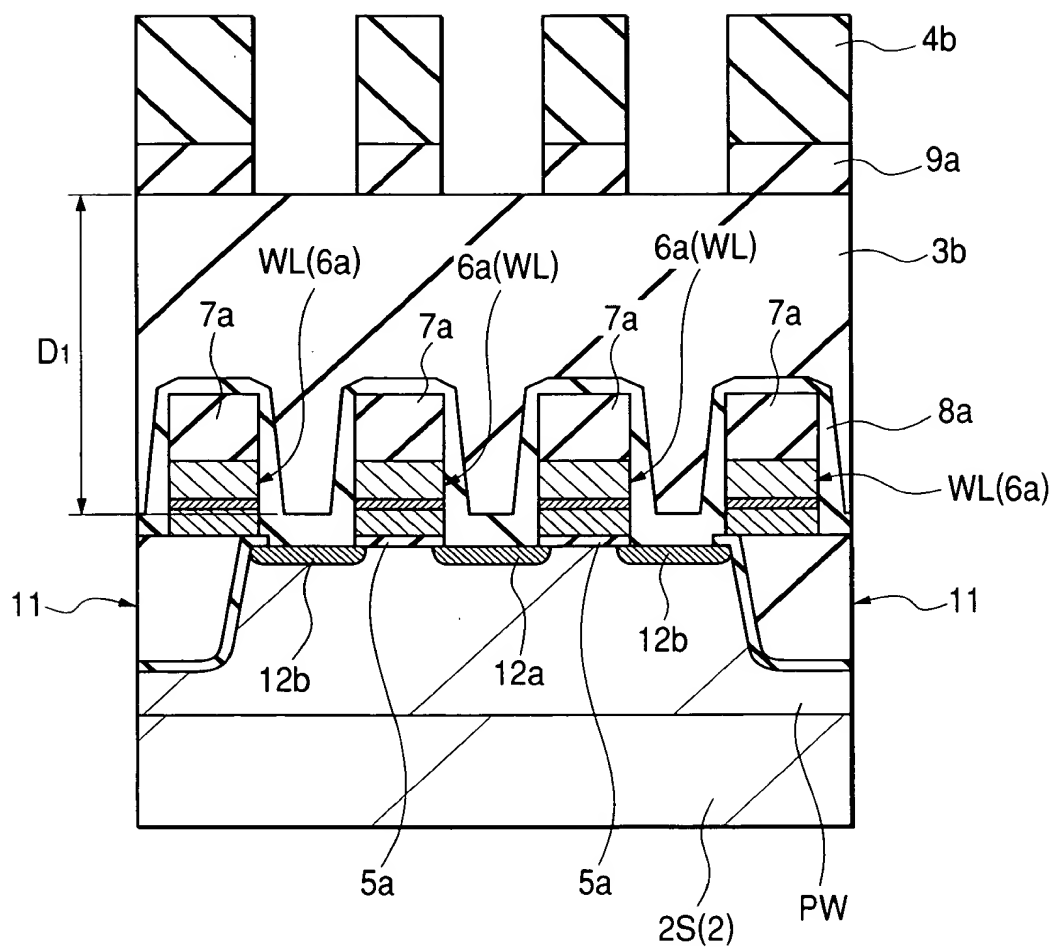


FIG. 4(a)

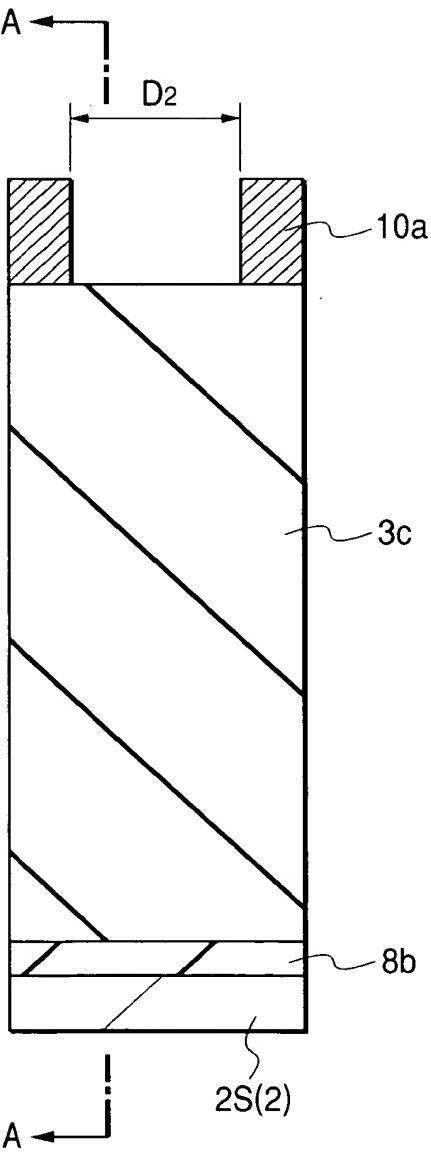
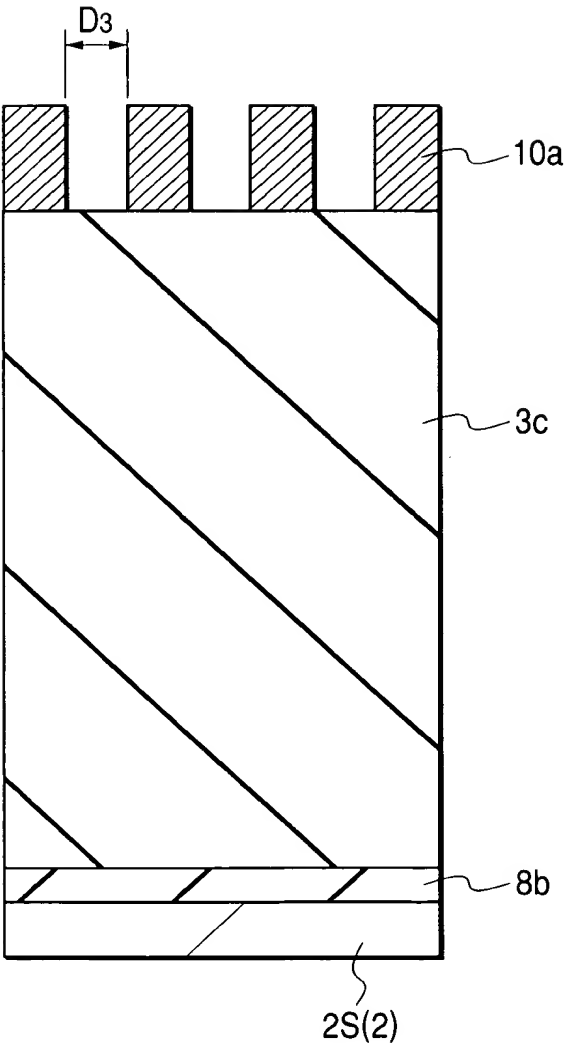
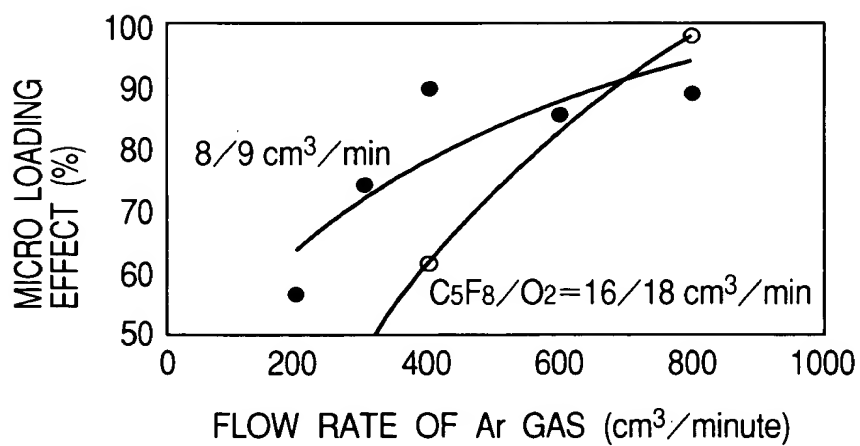


FIG. 4(b)



**FIG. 6**



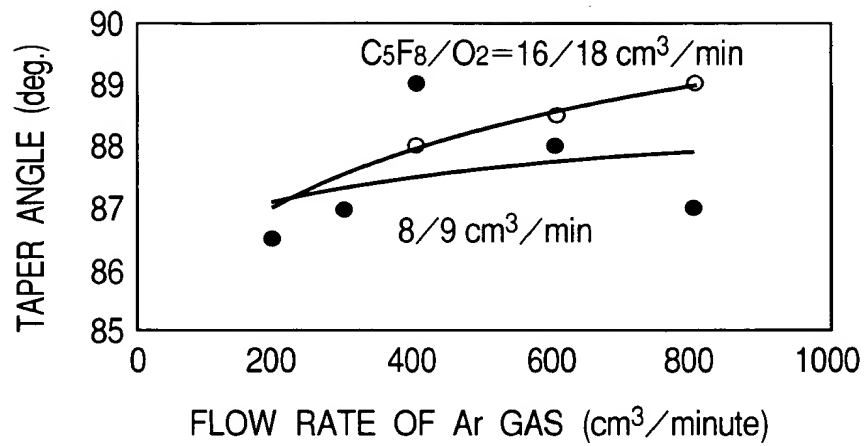
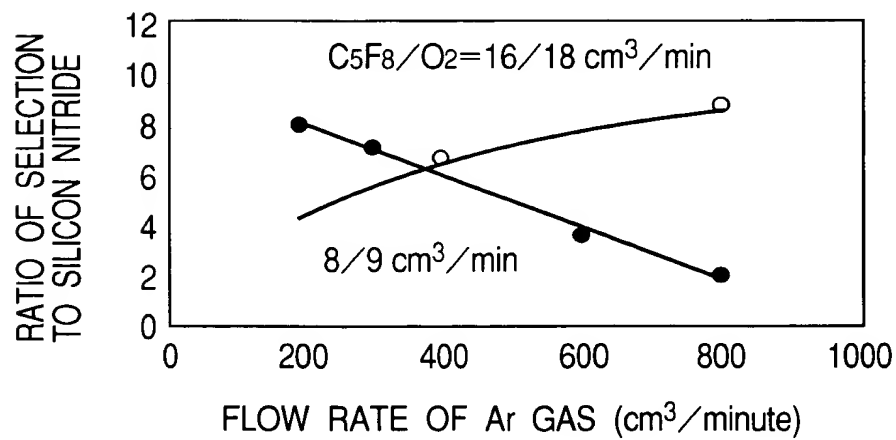
*FIG. 8(a)**FIG. 8(b)*

FIG. 9(a)

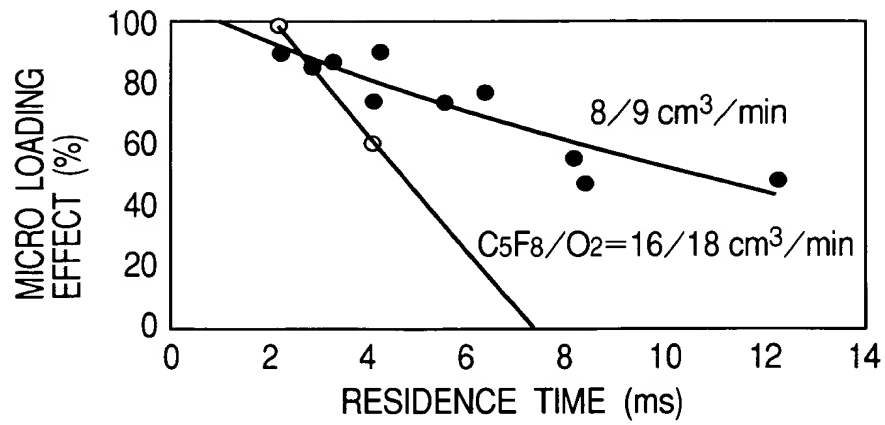


FIG. 9(b)

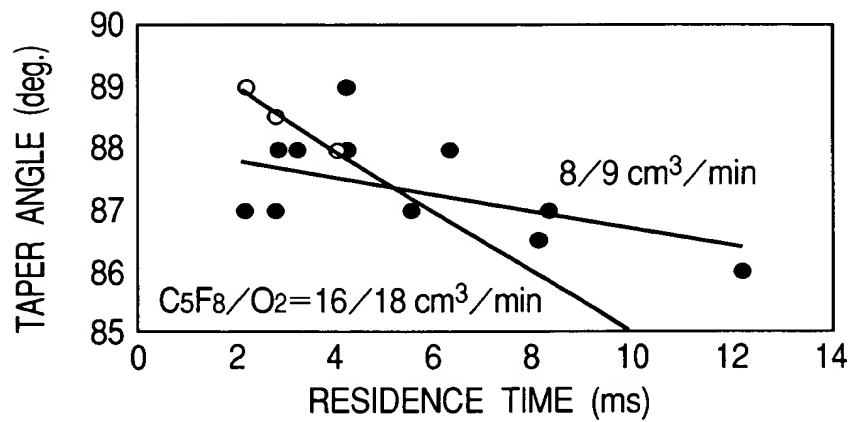


FIG. 9(c)

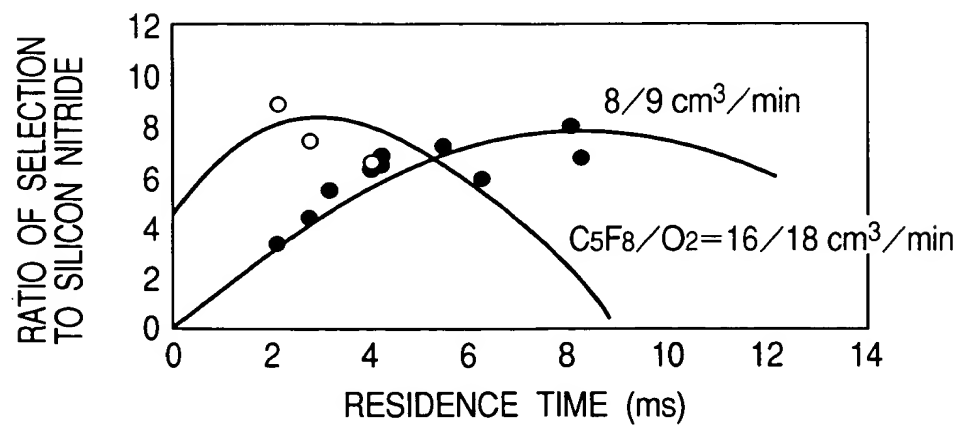


FIG. 10(a)

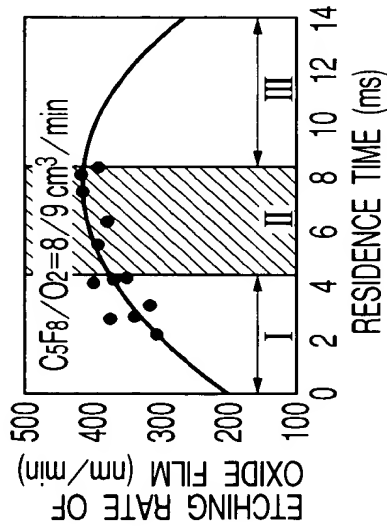


FIG. 10(b)

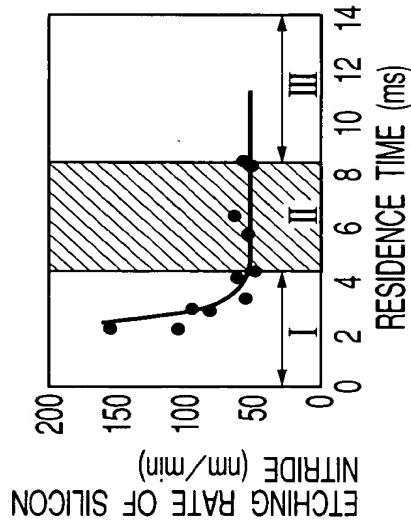


FIG. 10(c)

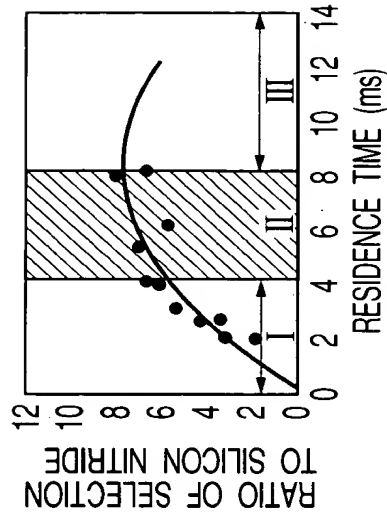


FIG. 10(d)

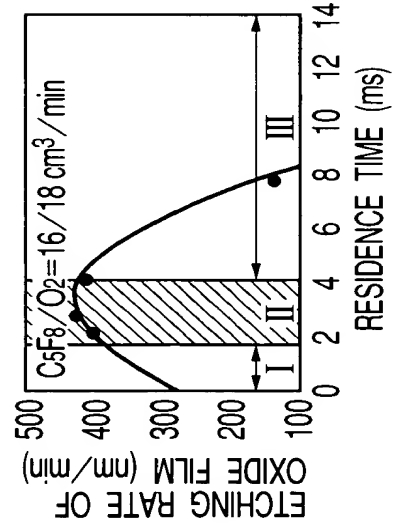


FIG. 10(e)

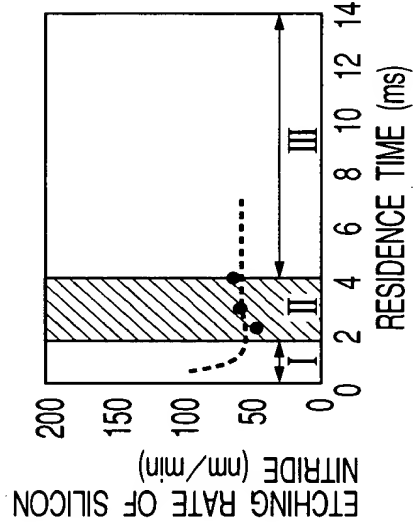
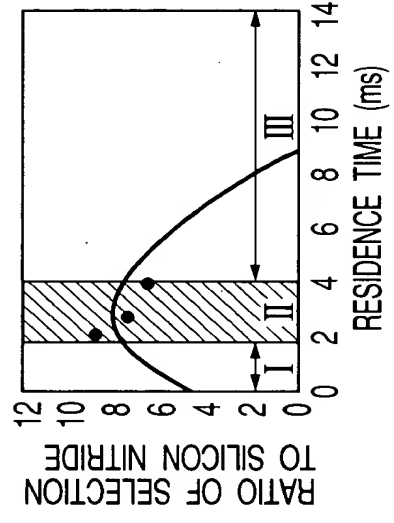
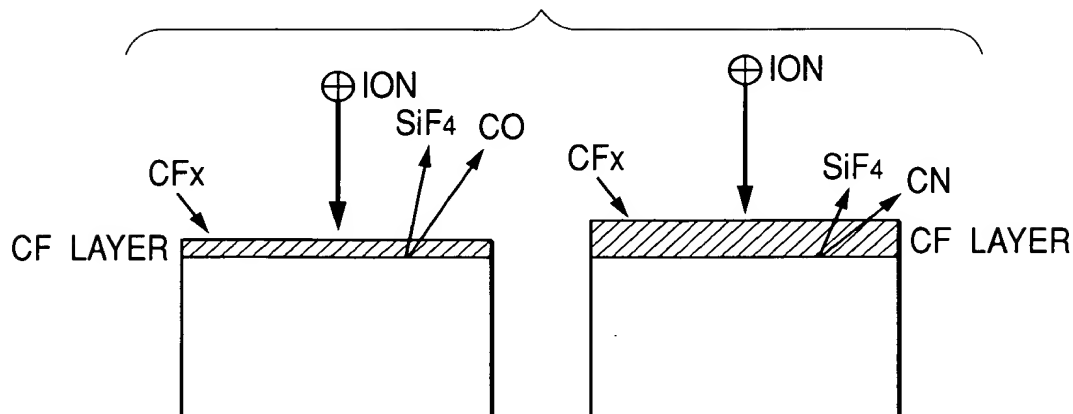
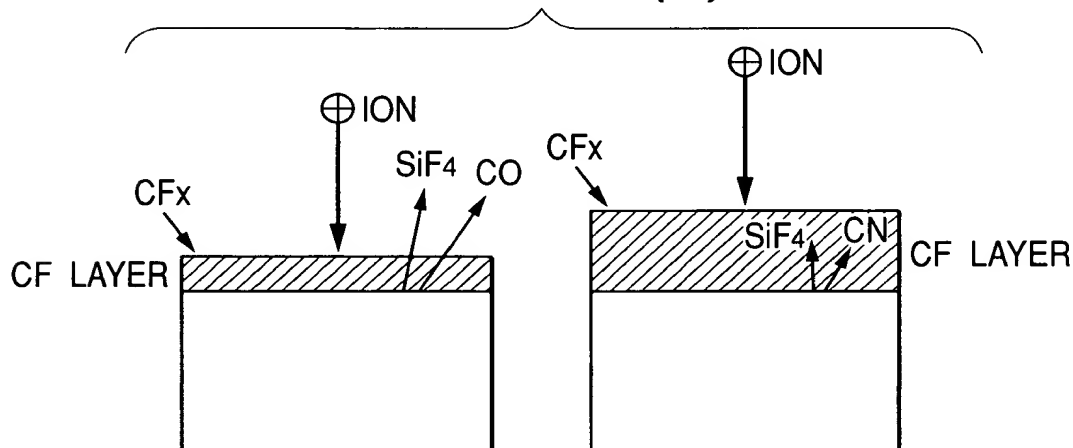
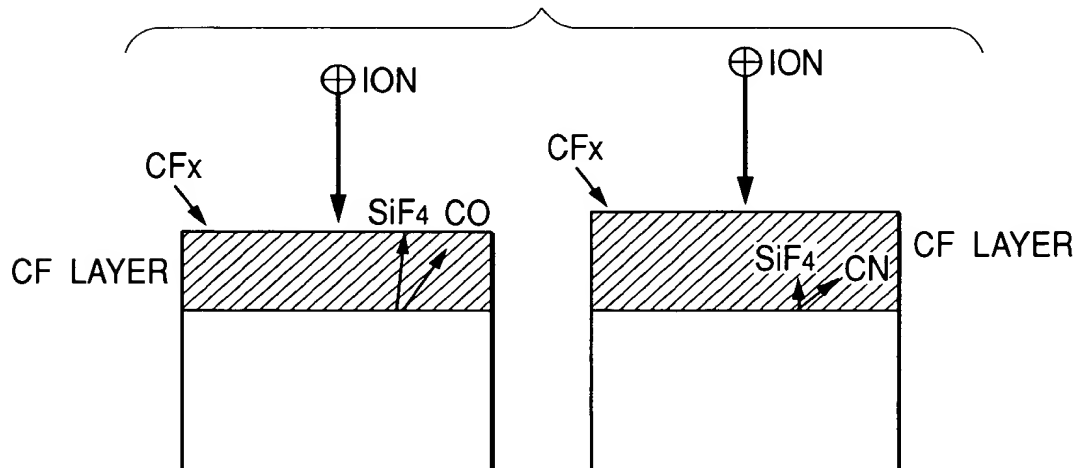
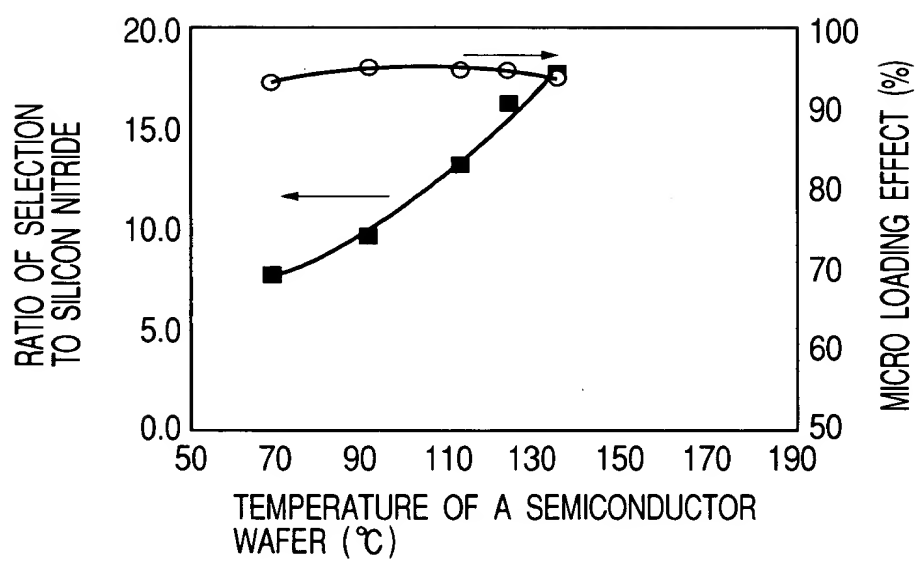


FIG. 10(f)





*FIG. 11(a)**FIG. 11(b)**FIG. 11(c)*

*FIG. 12*

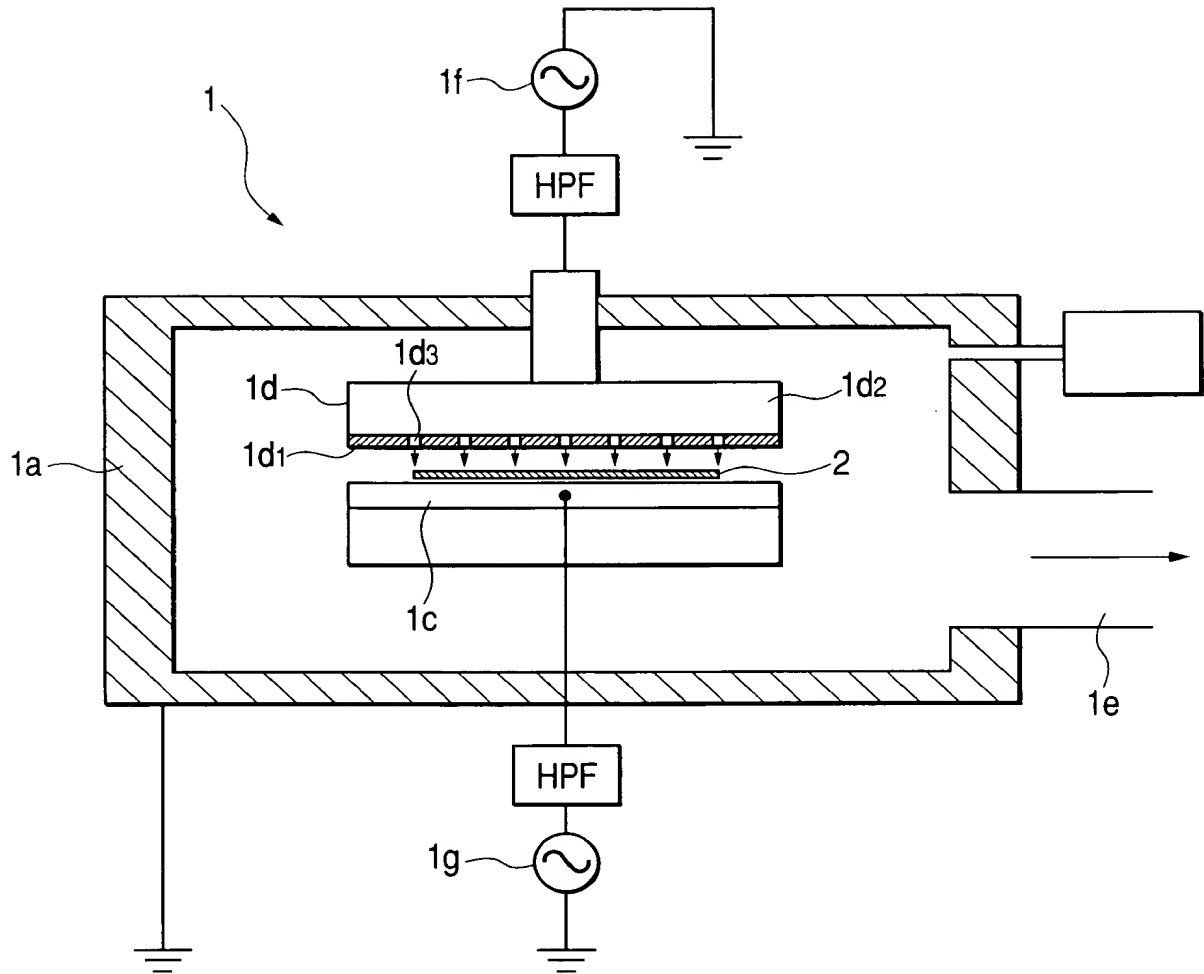
*FIG. 13*

PARAMETERS			
PRESSURE	[Pa]		2.66
RF POWER	UPPER PORTION	[W]	800
	LOWER PORTION	[W]	700
FLOW RATE OF C <sub>5</sub> F <sub>8</sub>	[cm <sup>3</sup> /minute]		16
FLOW RATE OF O <sub>2</sub>	[cm <sup>3</sup> /minute]		18
FLOW RATE OF Ar	[cm <sup>3</sup> /minute]		800
ELECTRODE TEMPERATURE			
	UPPER PORTION	( °C )	60
	LOWER PORTION	( °C )	20
TEMPERATURE OF WALL SURFACE	[ °C ]		50
ELECTRODE GAP	[mm]		21

*FIG. 14*

PARAMETERS			
PRESSURE	[Pa]		2.66
RF POWER	UPPER PORTION	[W]	1800
	LOWER PORTION	[W]	1500
FLOW RATE OF C <sub>5</sub> F <sub>8</sub>	[cm <sup>3</sup> /minute]		24
FLOW RATE OF O <sub>2</sub>	[cm <sup>3</sup> /minute]		28
FLOW RATE OF Ar	[cm <sup>3</sup> /minute]		700
ELECTRODE TEMPERATURE			
	UPPER PORTION	(°C)	60
	LOWER PORTION	(°C)	20
TEMPERATURE OF WALL SURFACE	[°C]		50
ELECTRODE GAP	[mm]		19

**FIG. 15**



**FIG. 16**

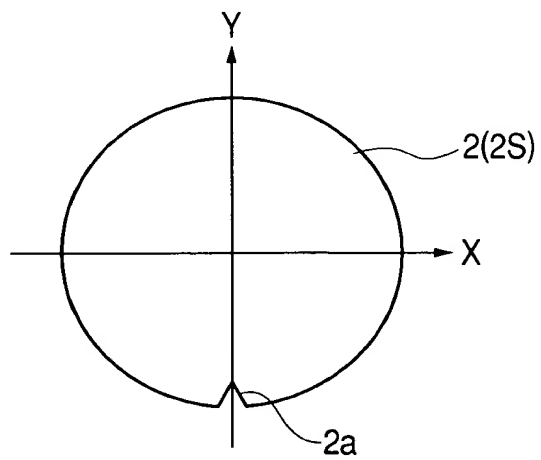


FIG. 17

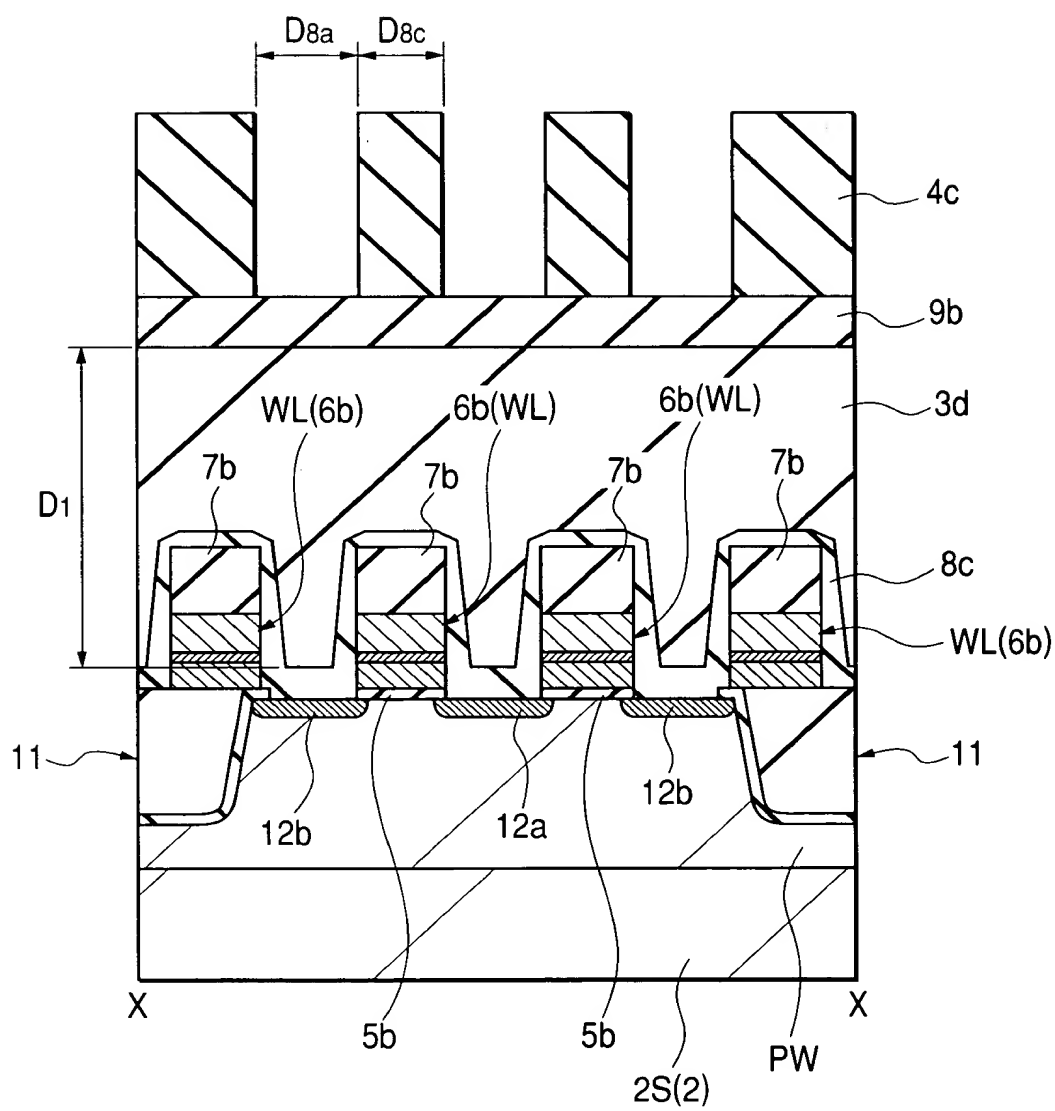
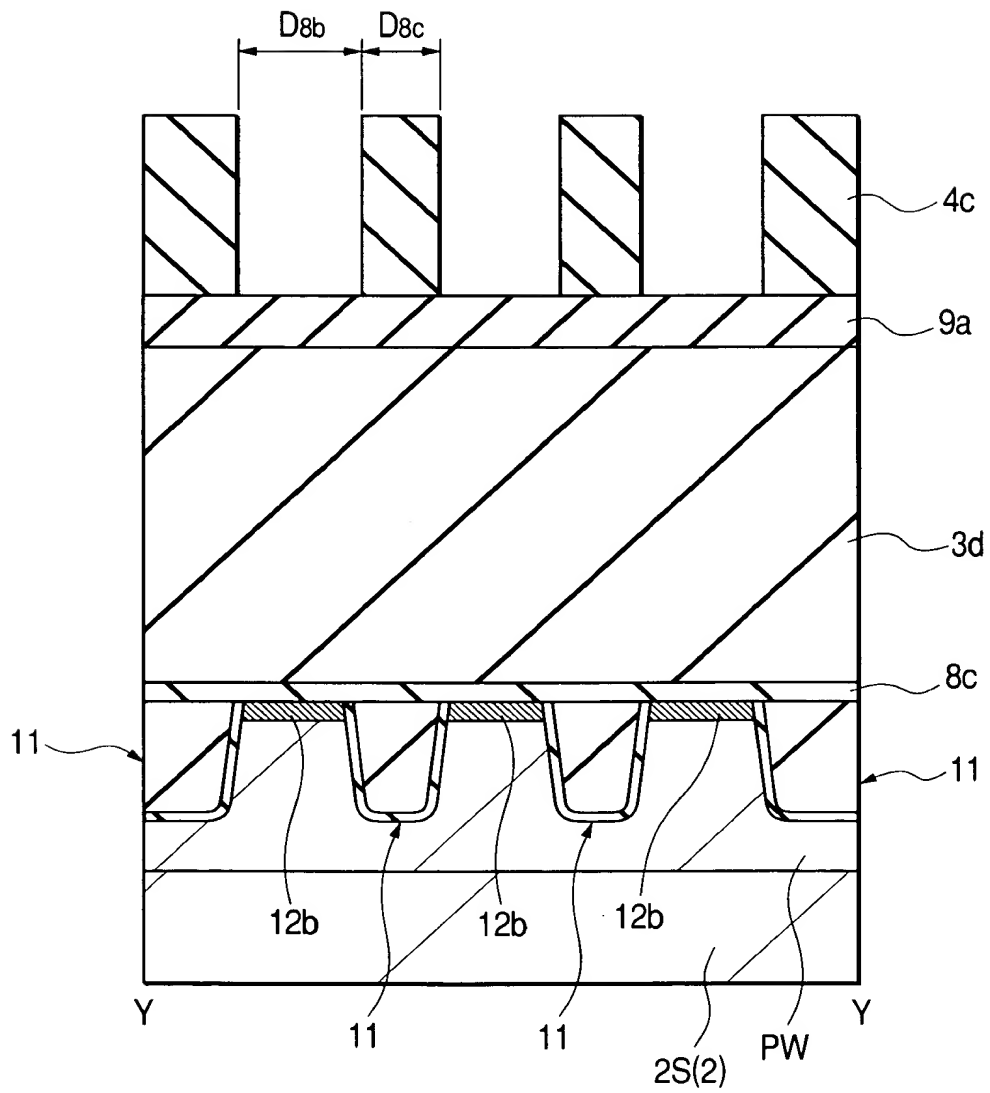


FIG. 18



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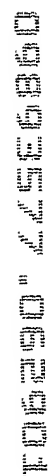




FIG. 20

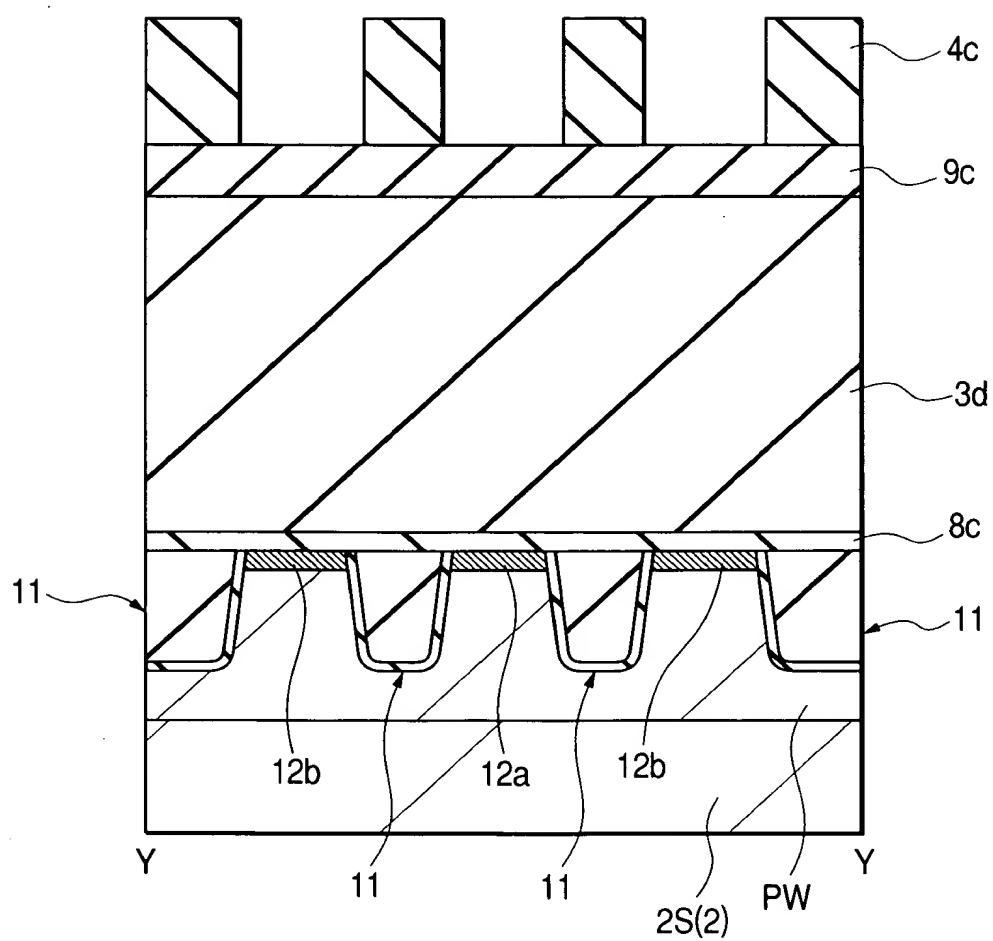


FIG. 20

[illegible]

FIG. 22

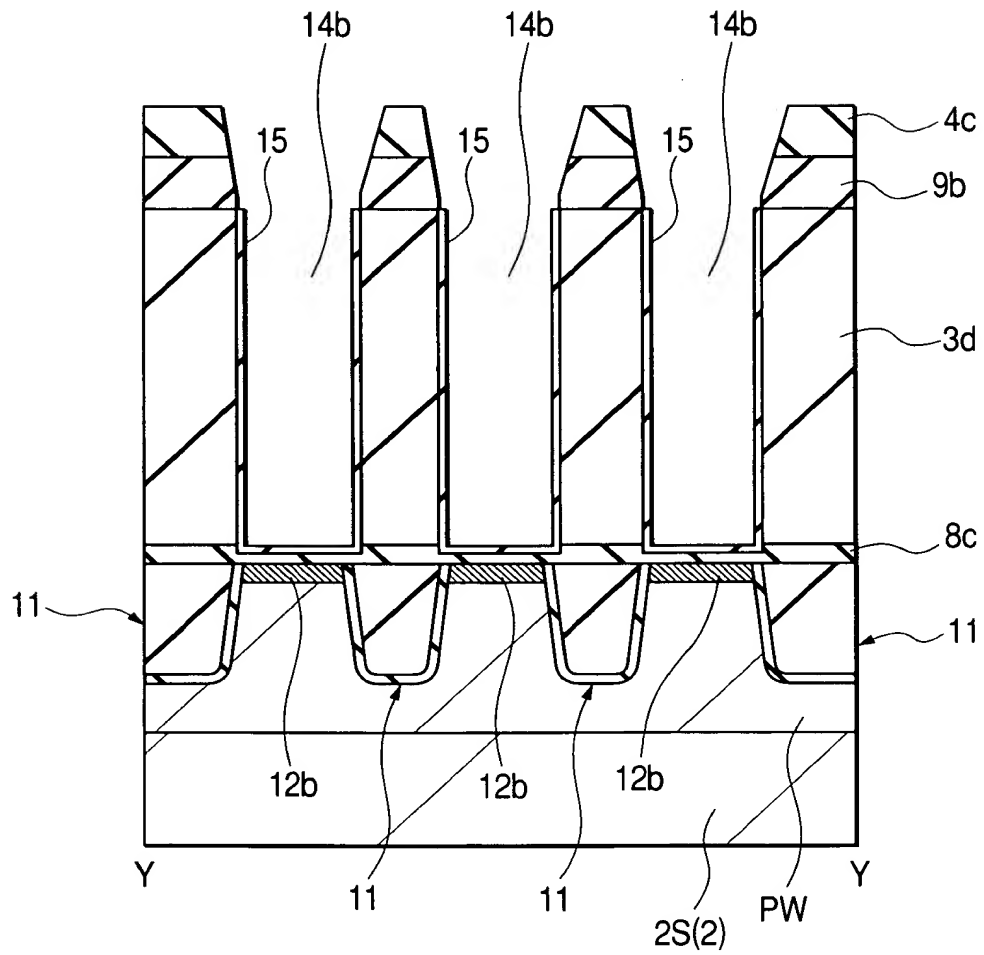


FIG. 23

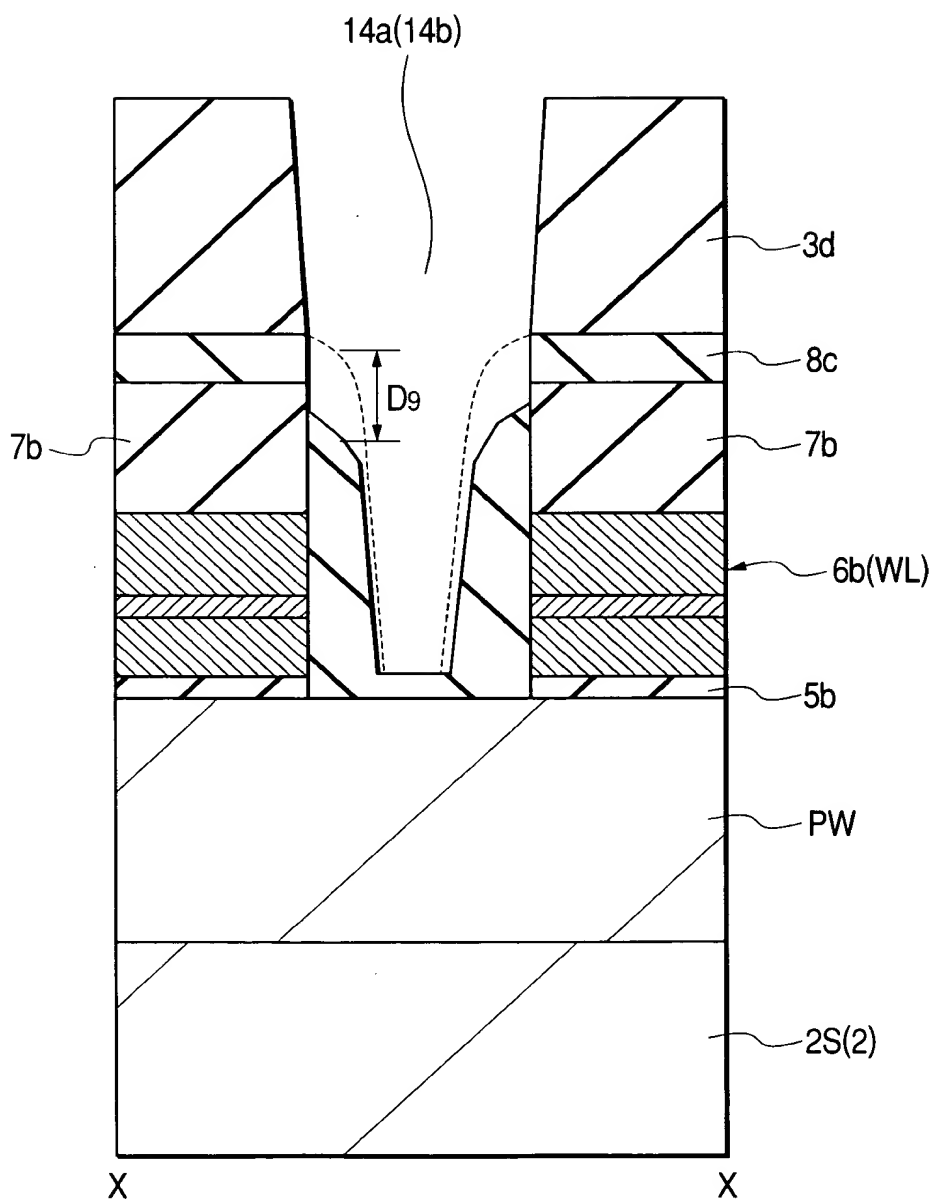
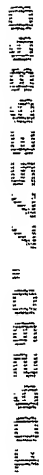


FIG. 23

**SECRET**



**FIG. 25**

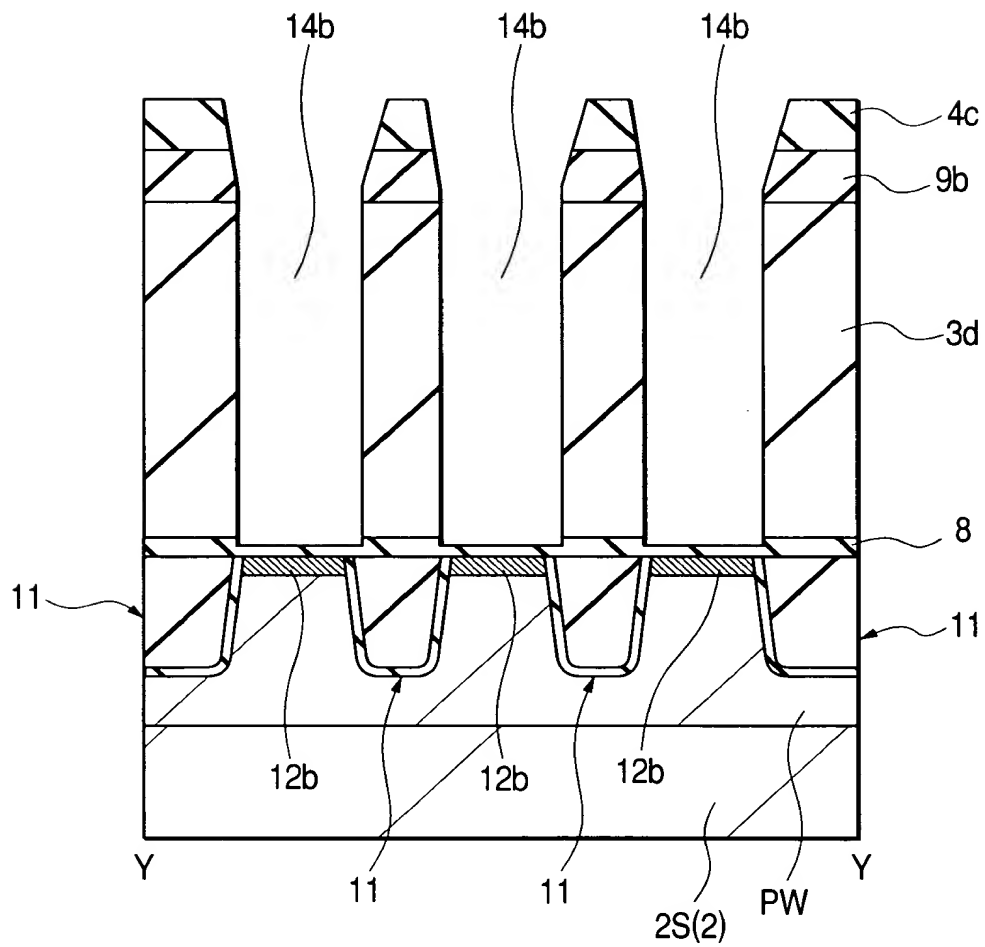


FIG. 26

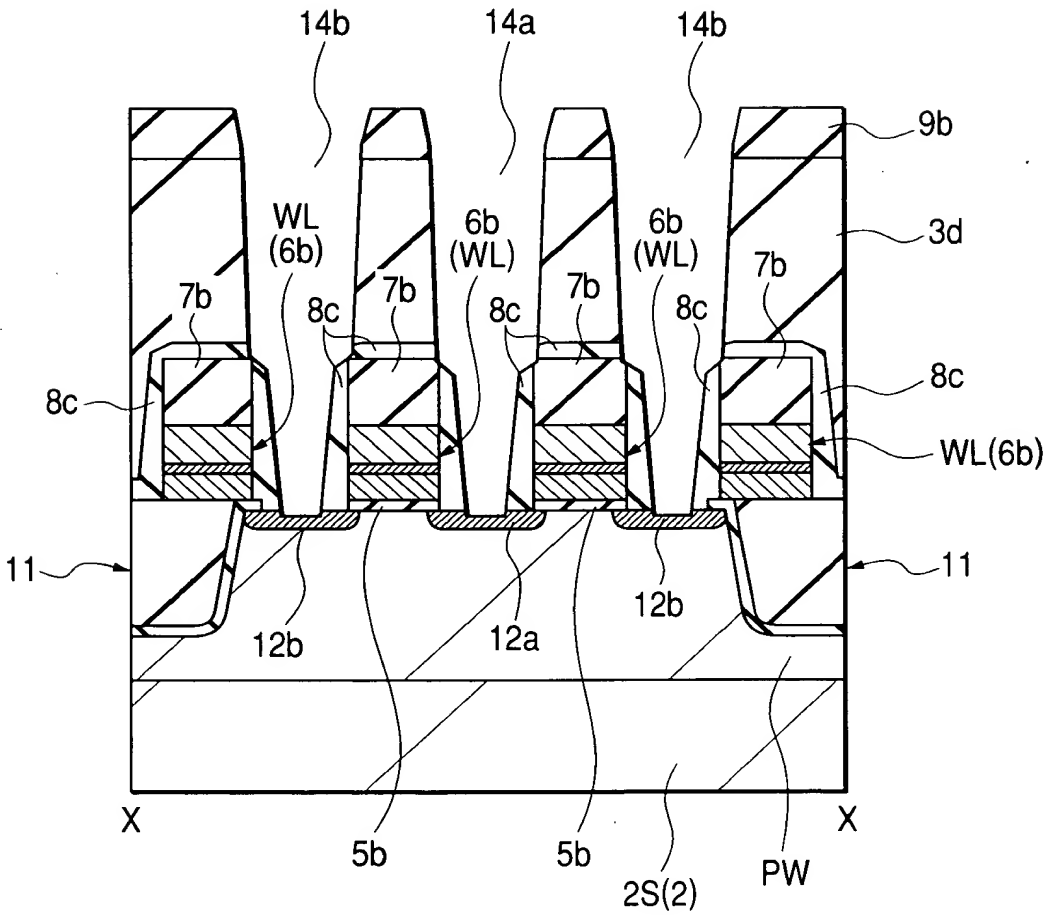


FIG. 26

FIG. 27

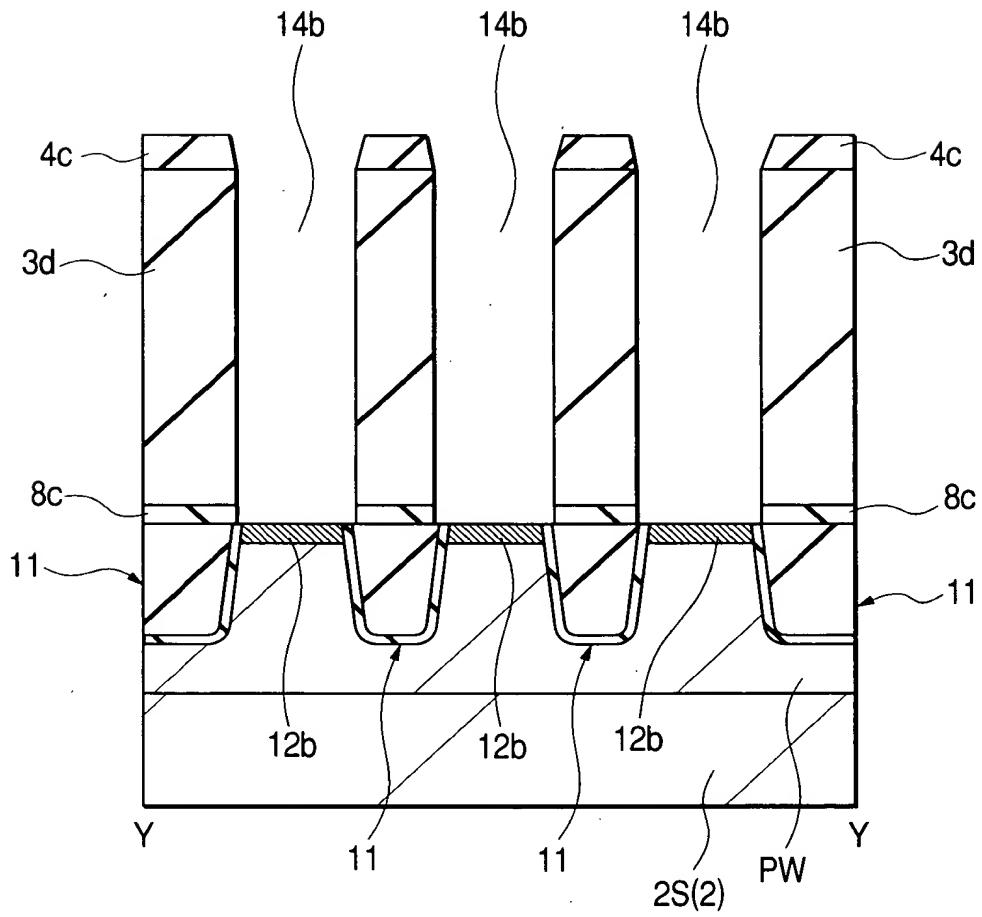
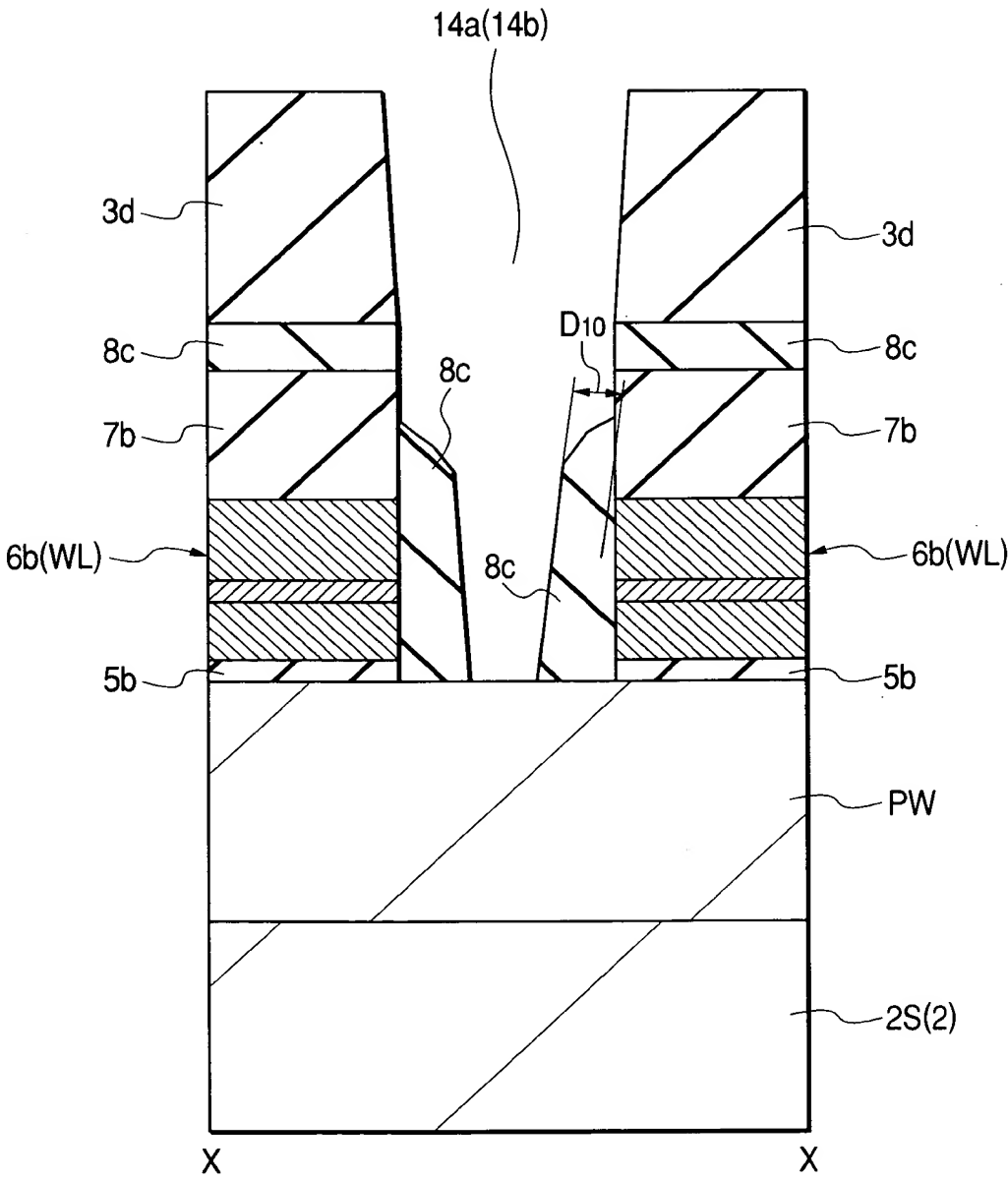


FIG. 27



FIG. 28



0989357.062901

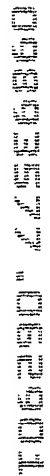
[illegible]

FIG. 30

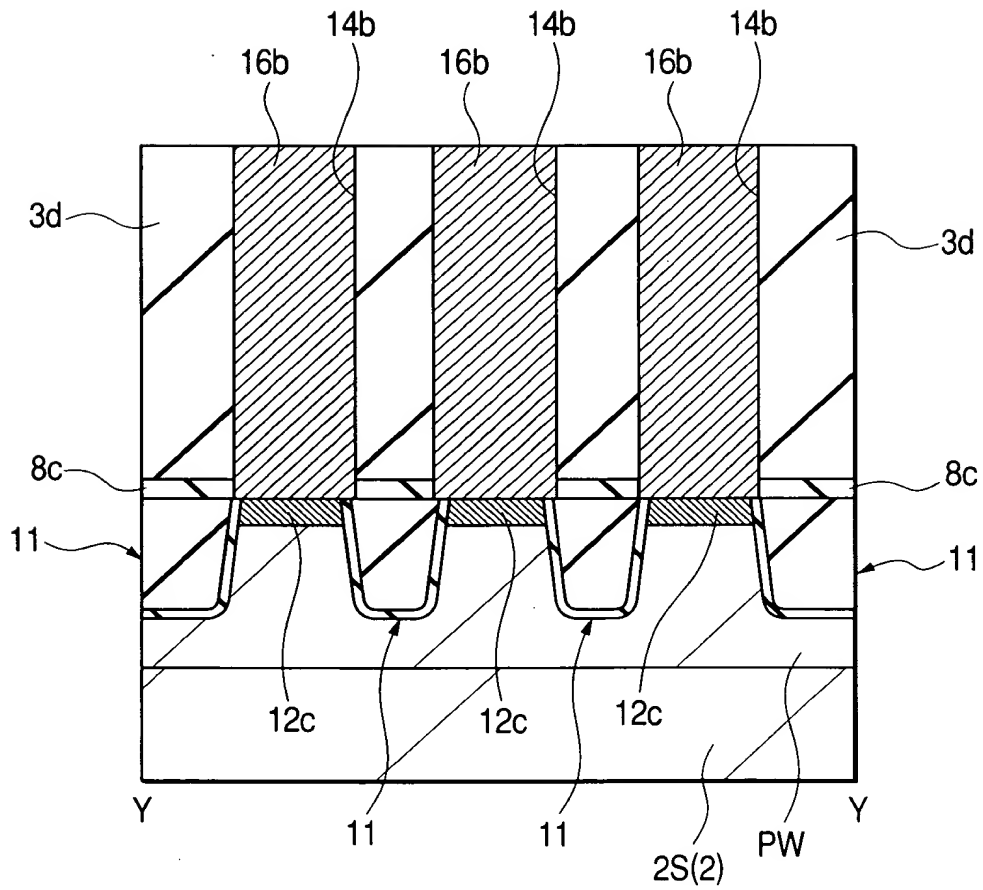


FIG. 31

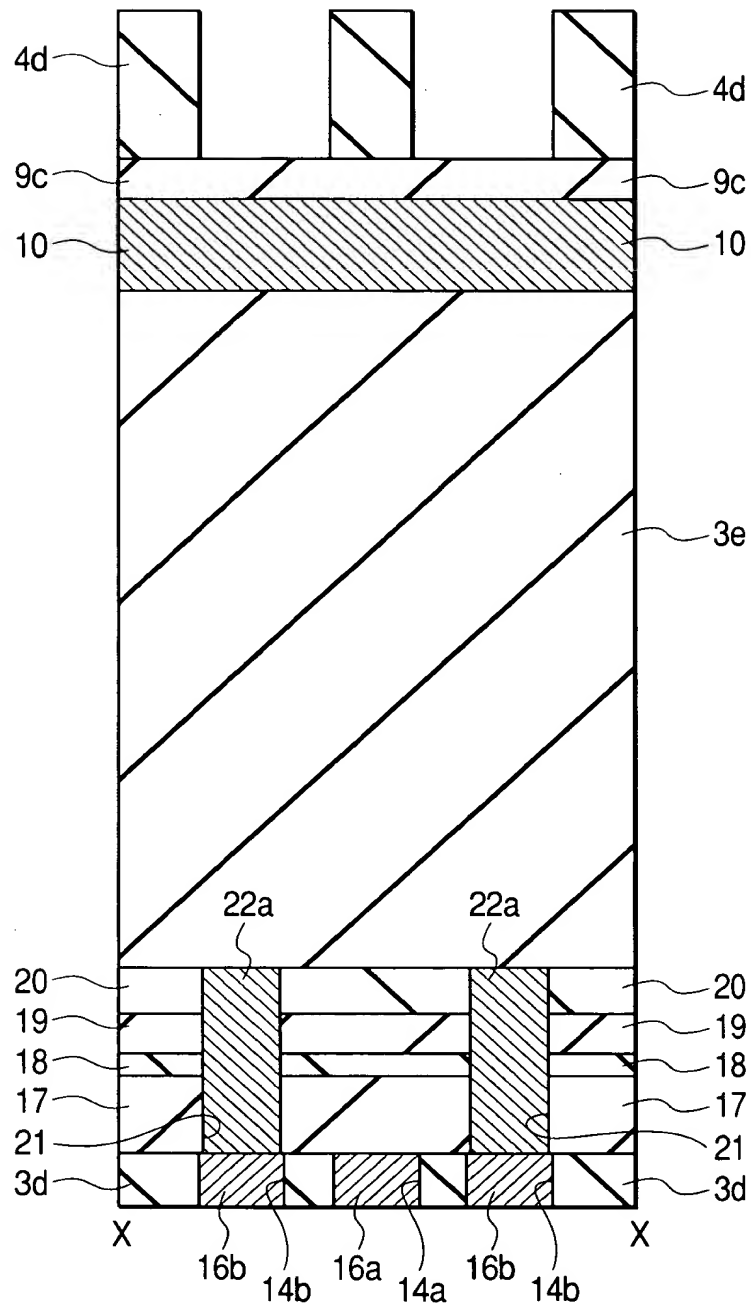


FIG. 32

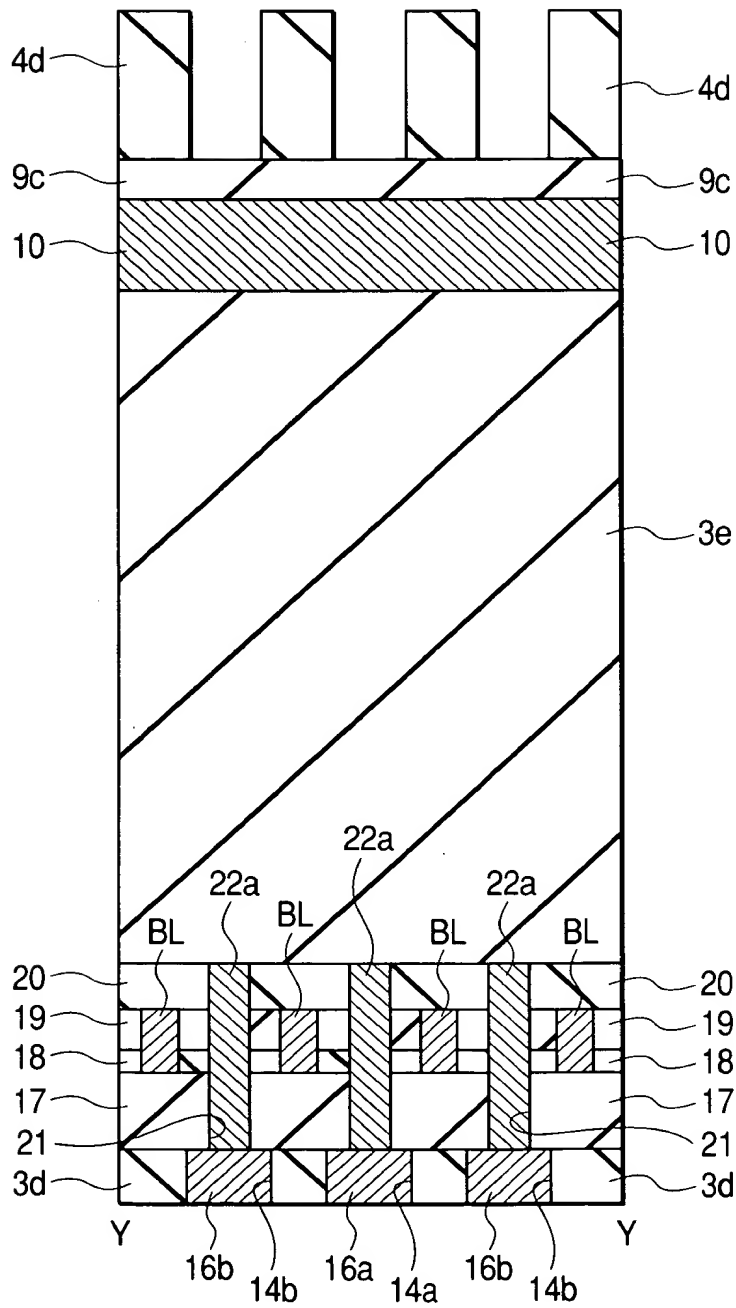


FIG. 33

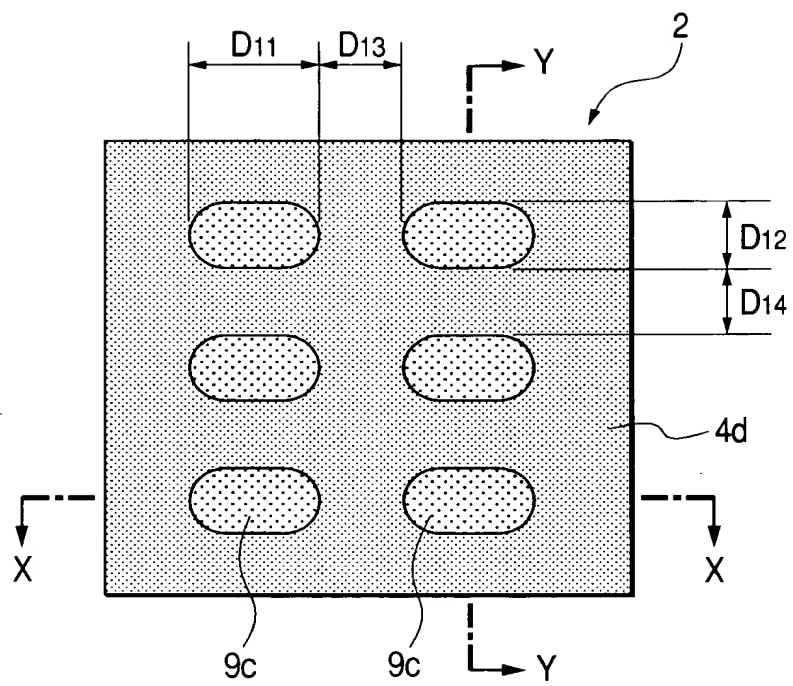


FIG. 34

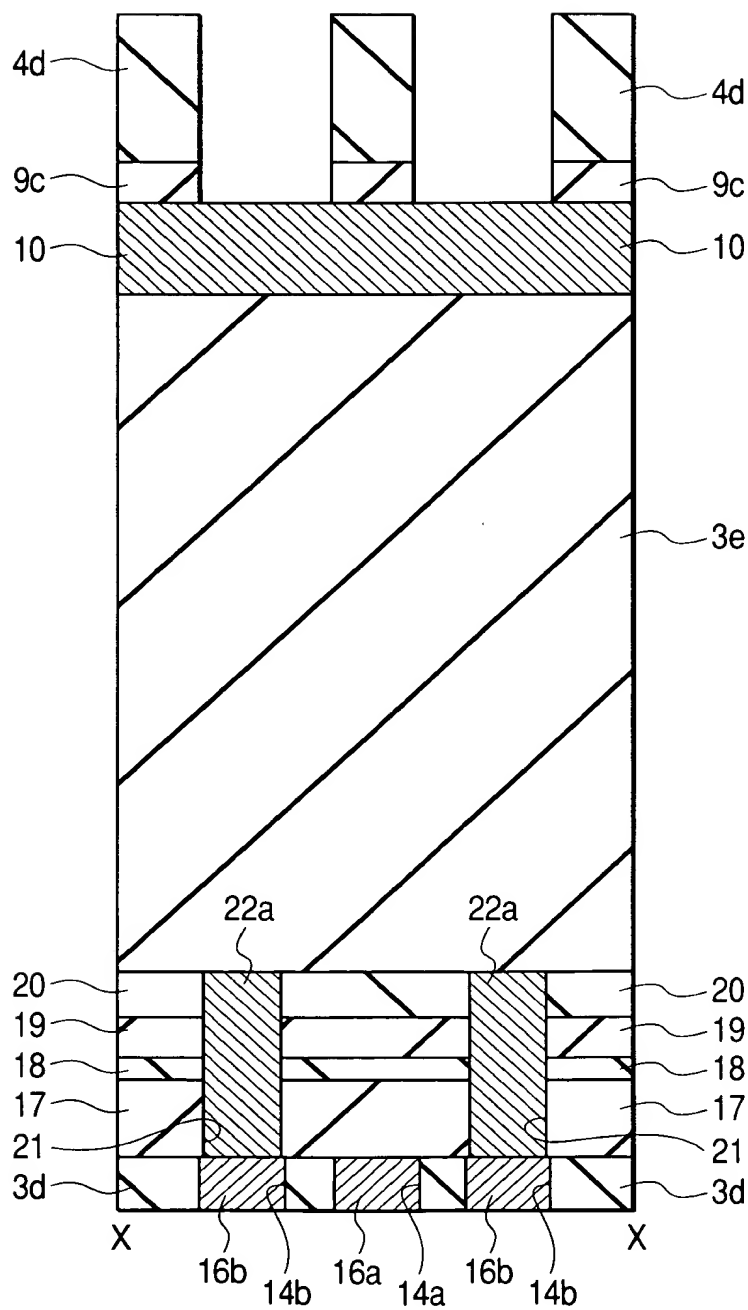


FIG. 35

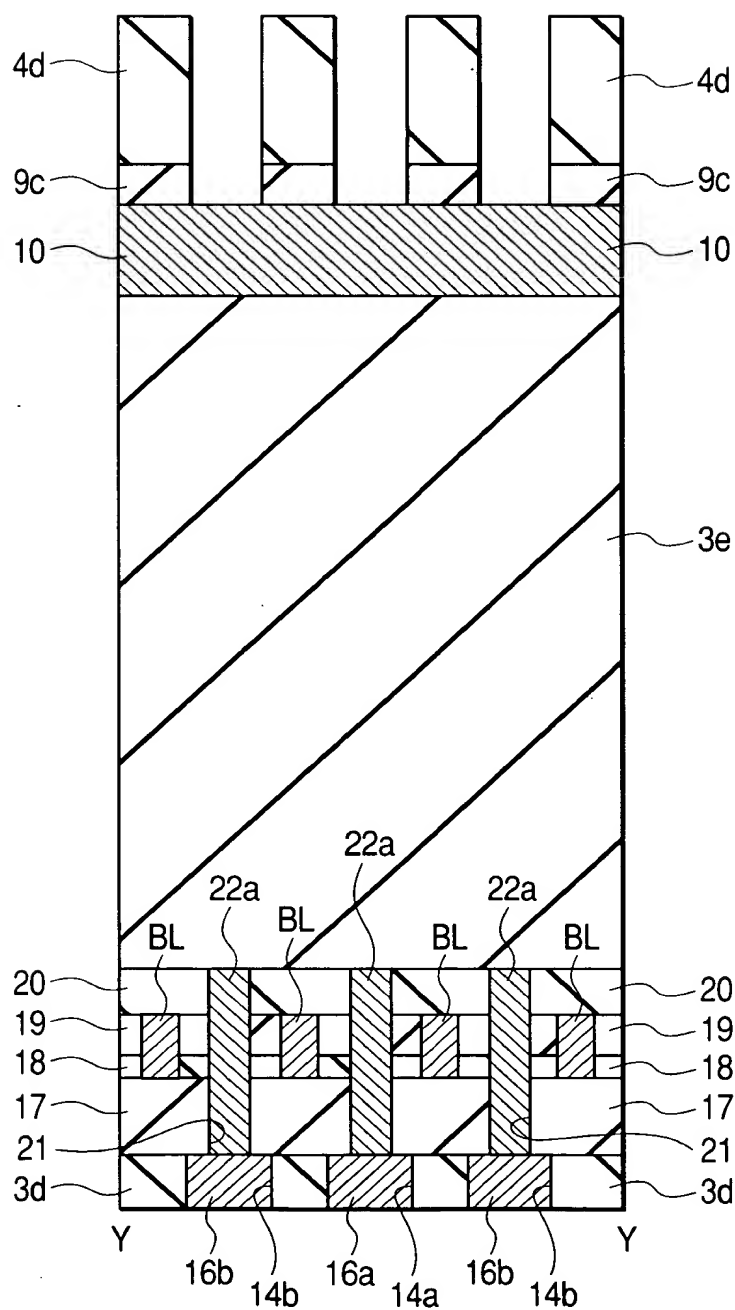
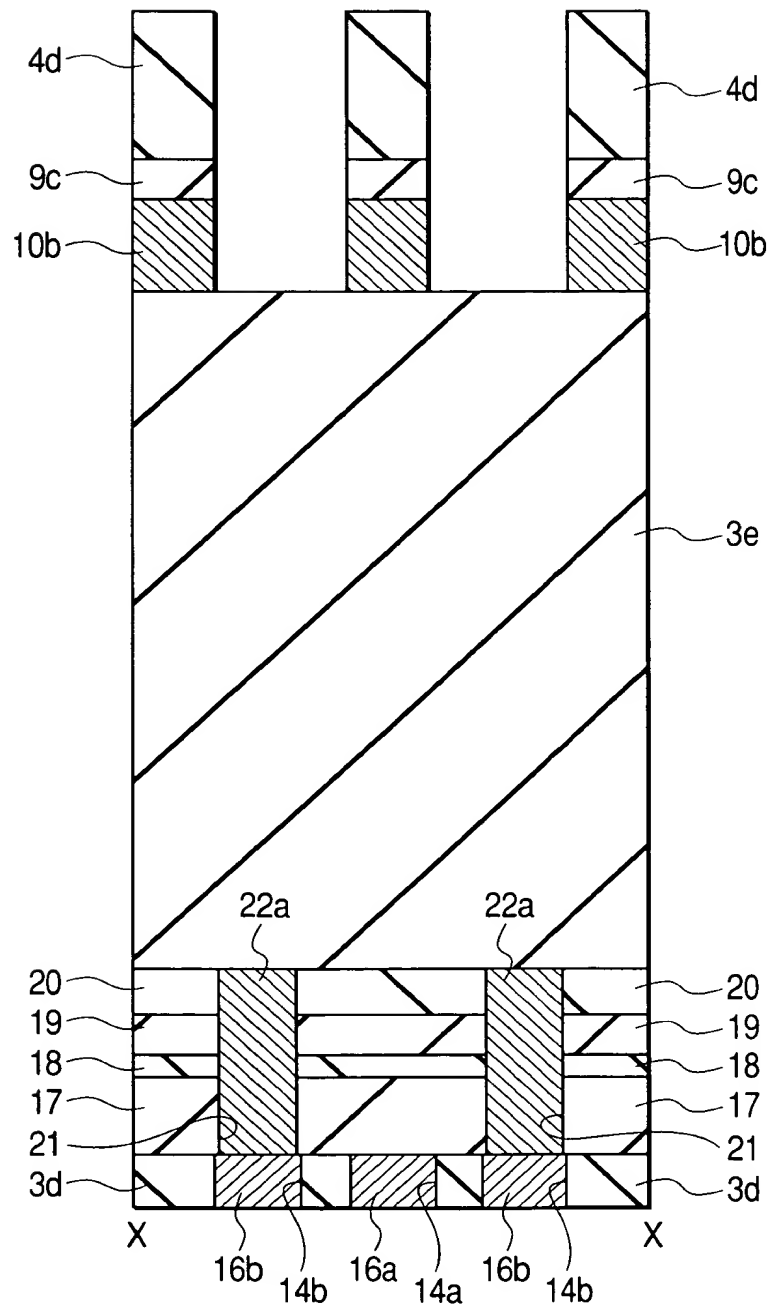




FIG. 36



09893577.062901

FIG. 37

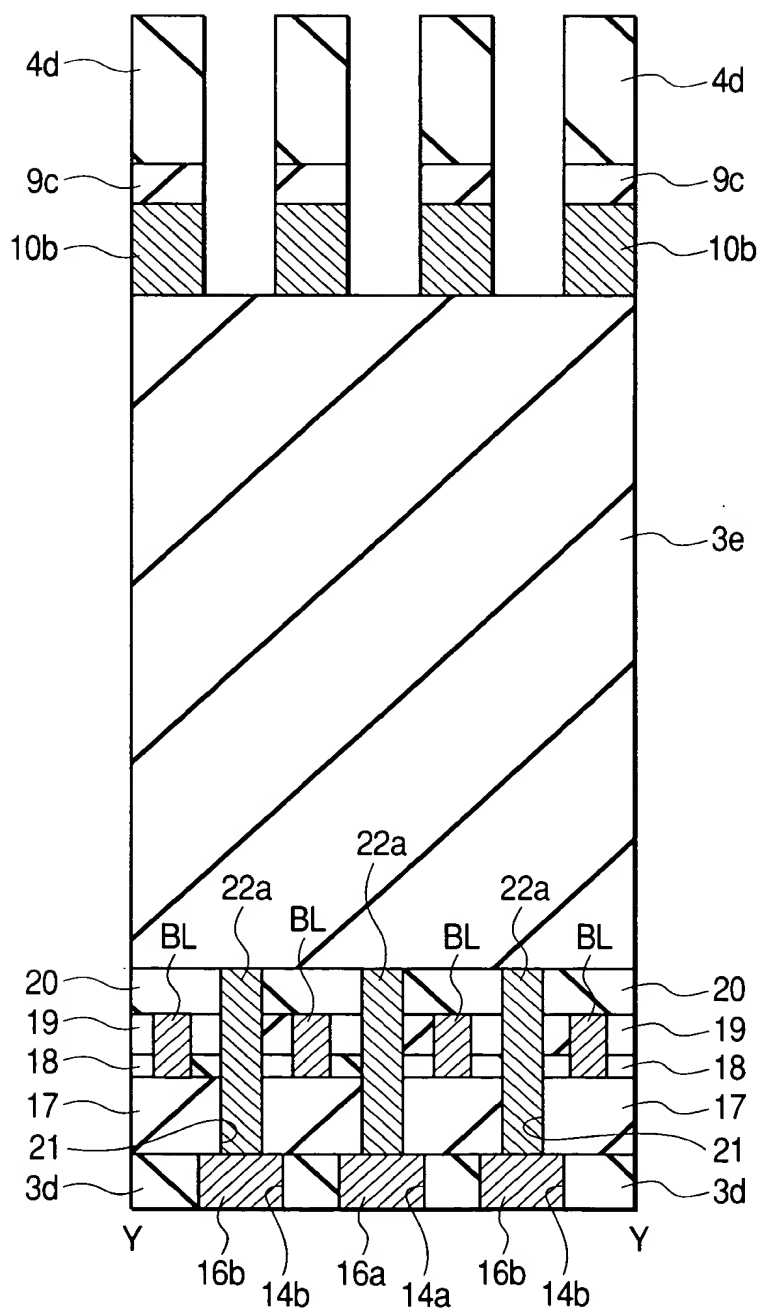


FIG. 38

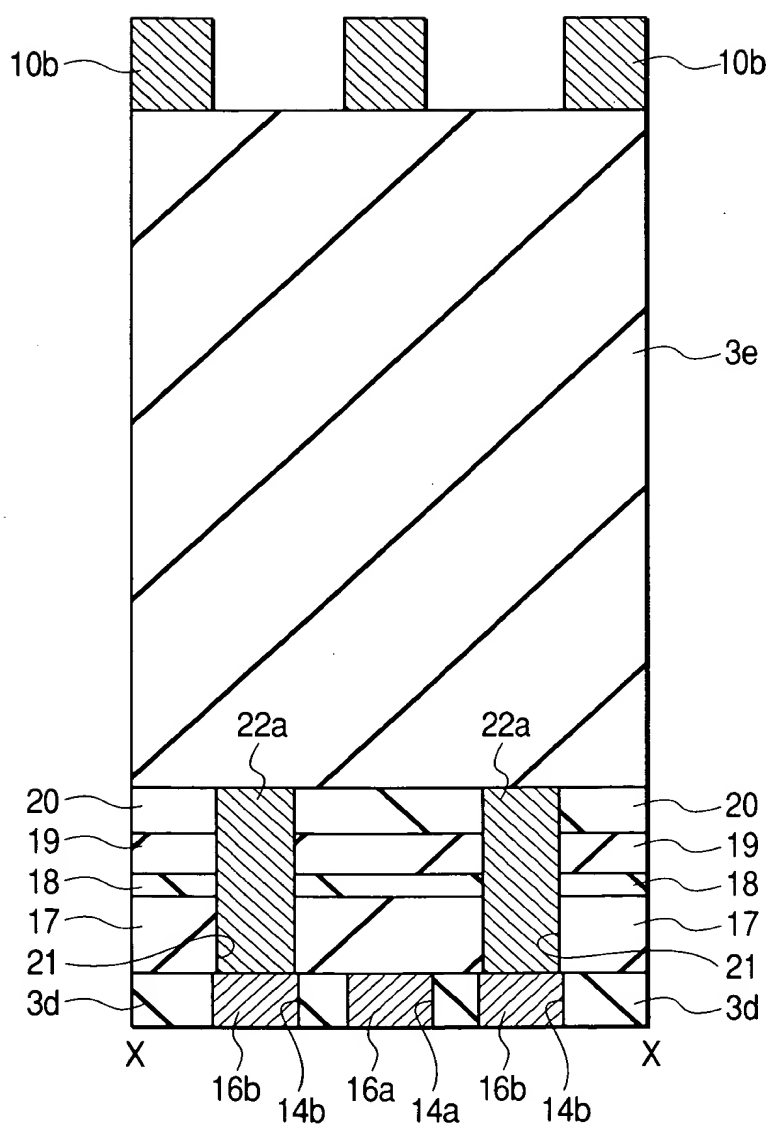


FIG. 39

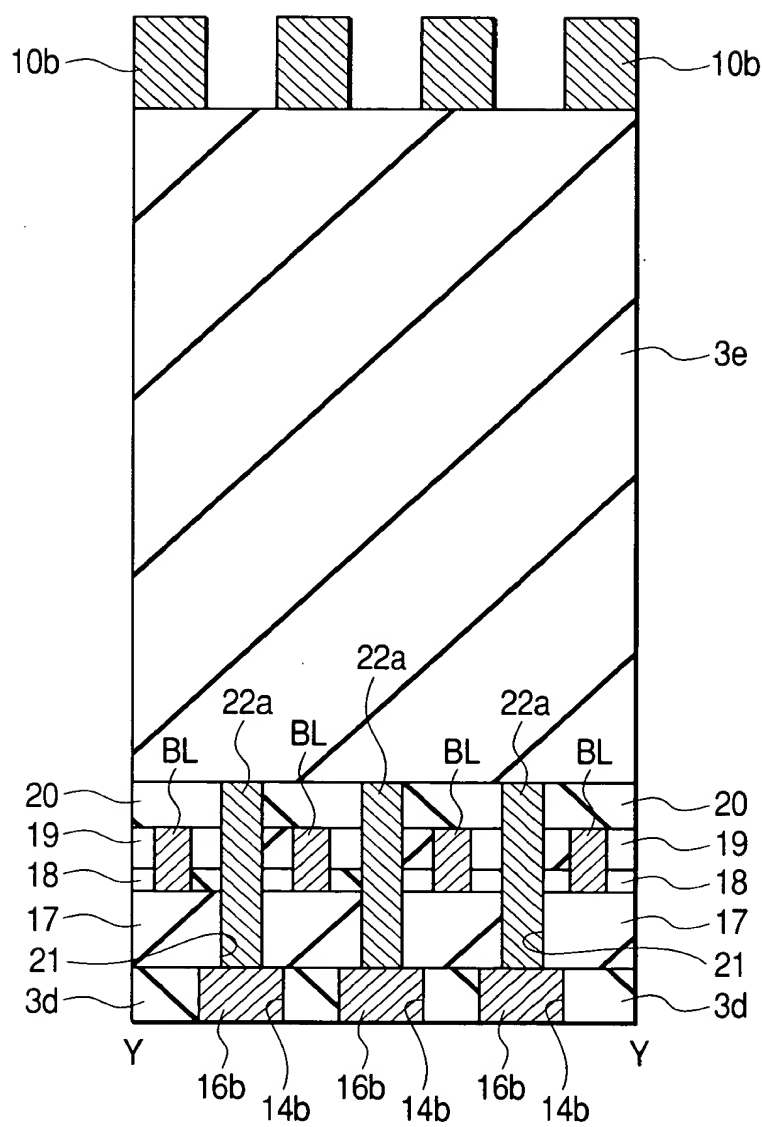


FIG. 39

FIG. 40

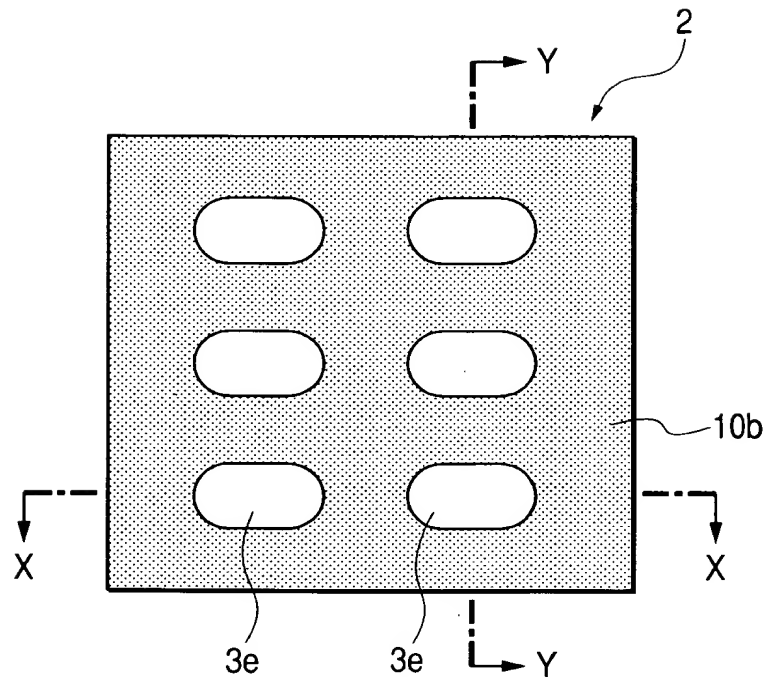
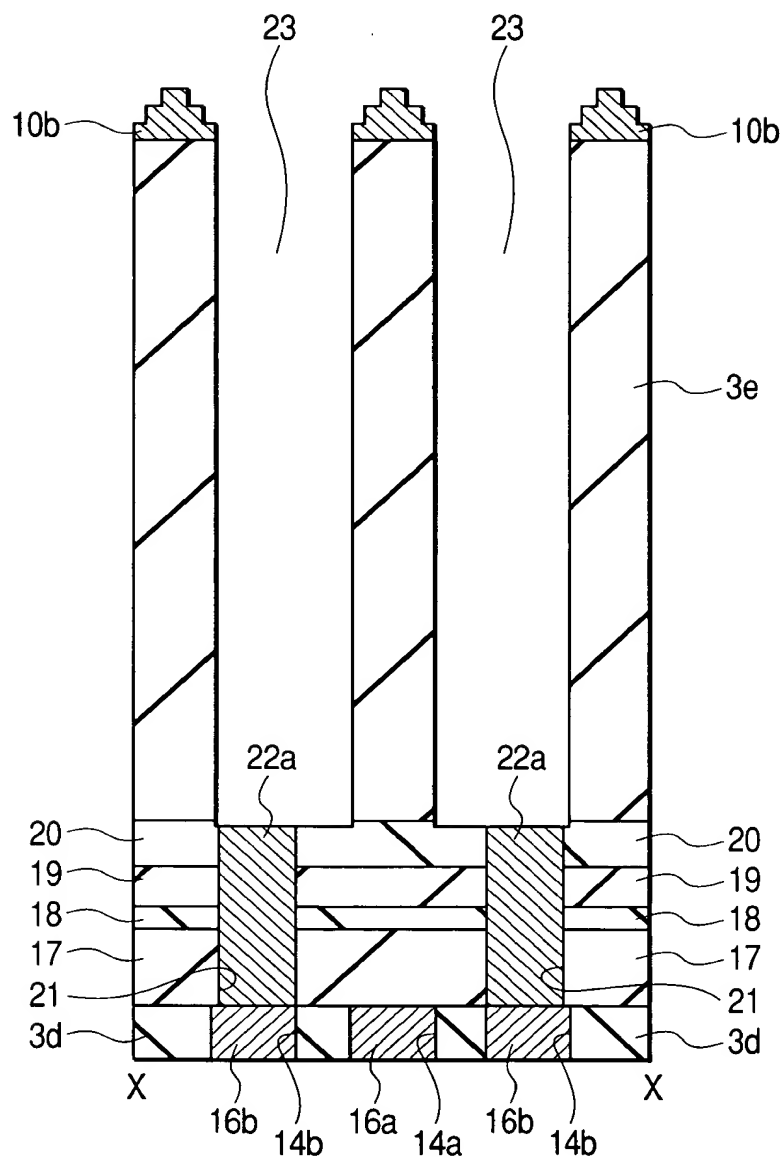


FIG. 41



[illegible]

FIG. 43

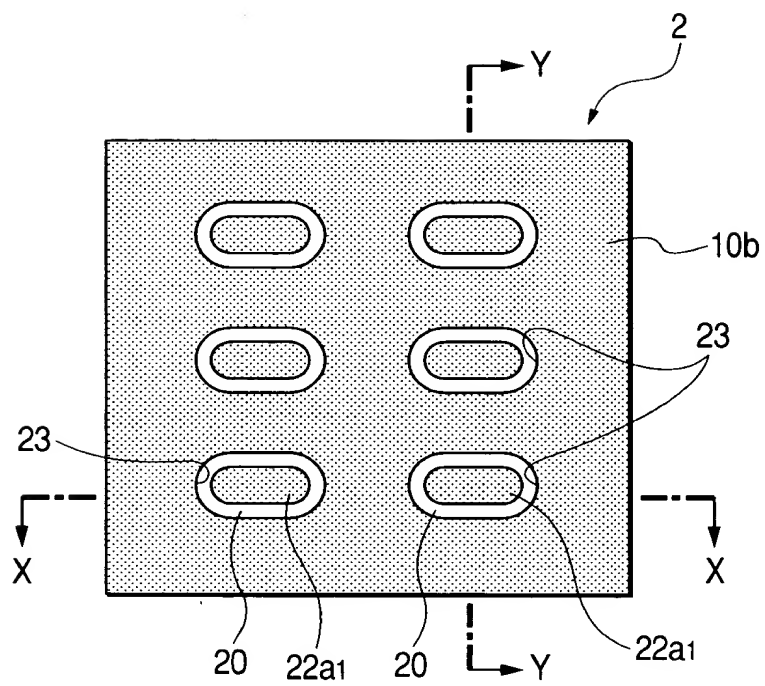




FIG. 44

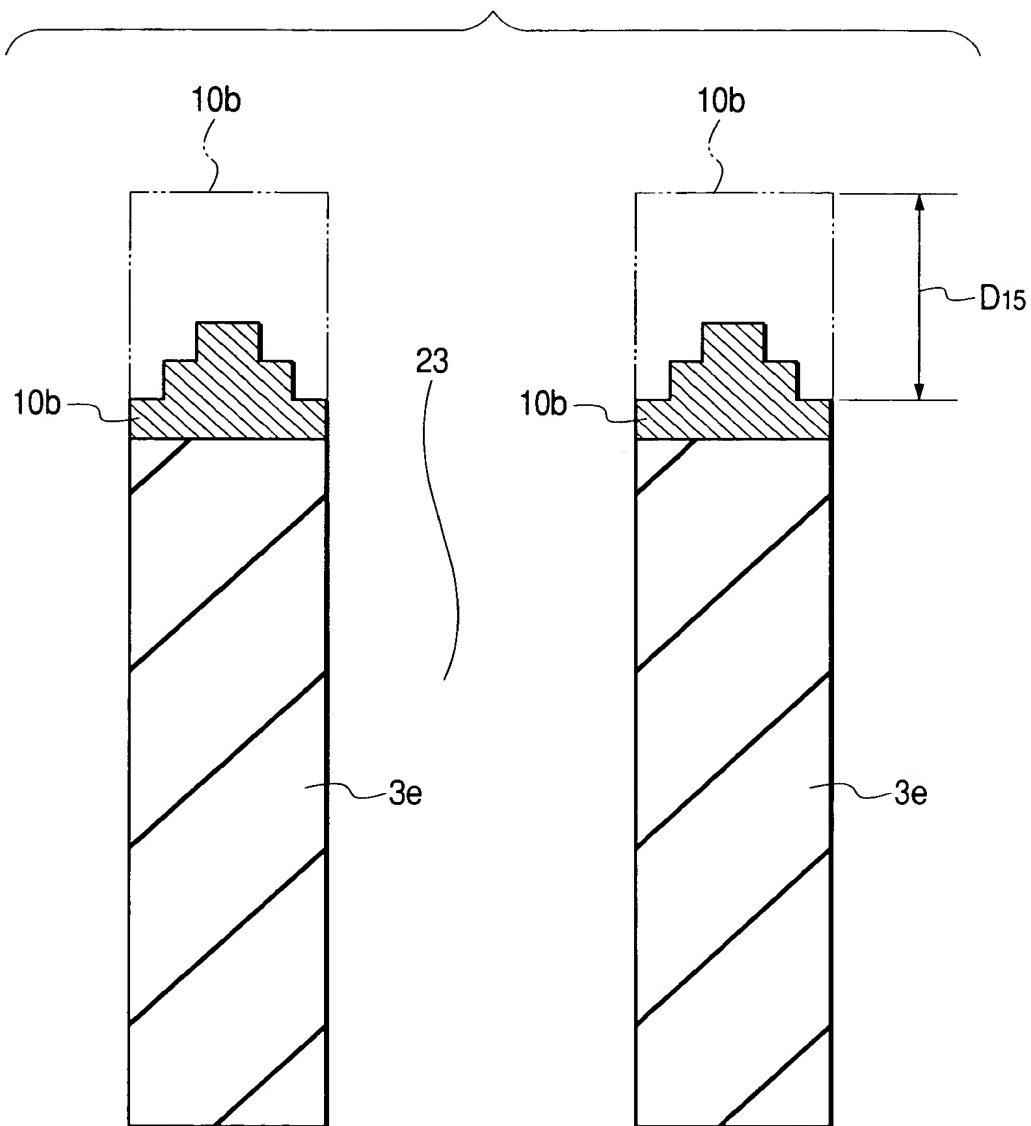
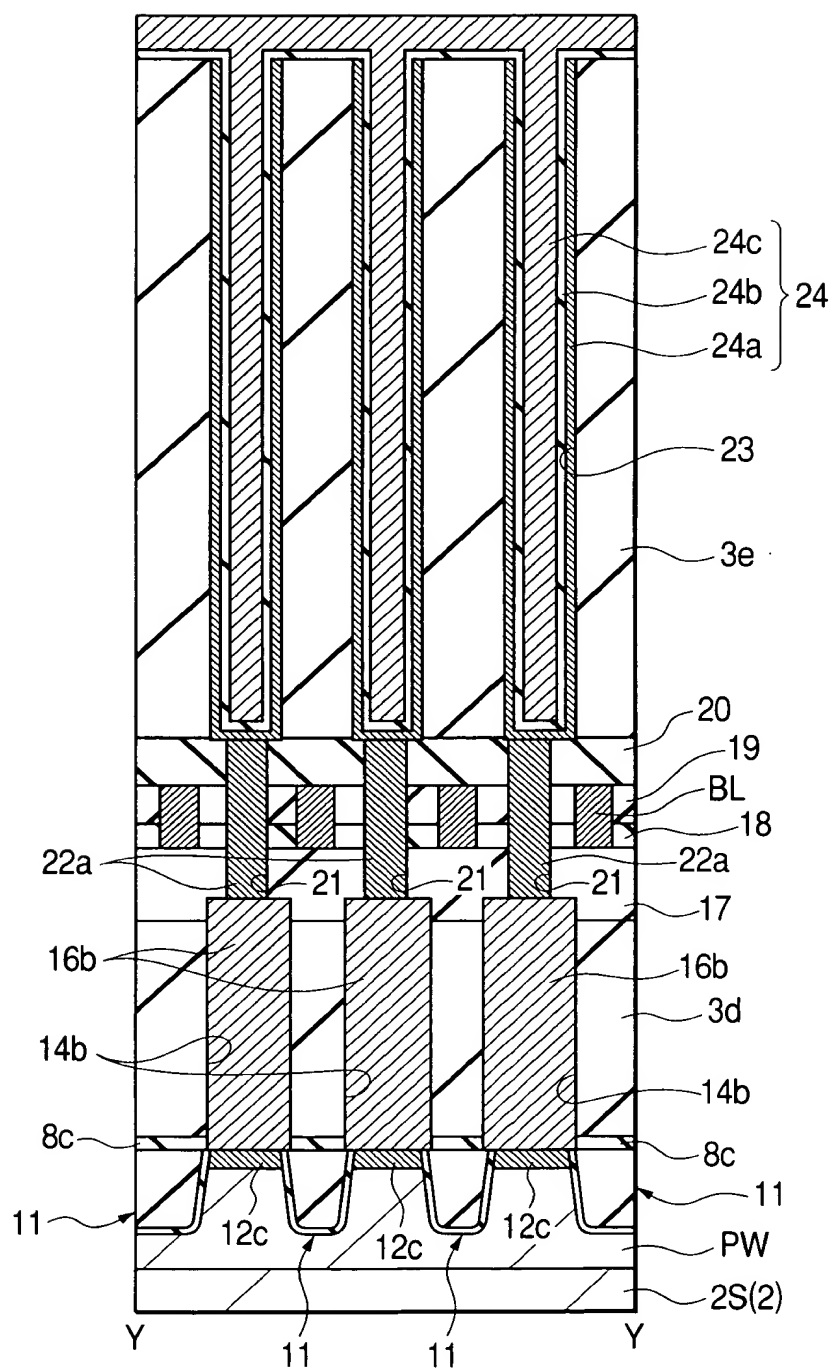


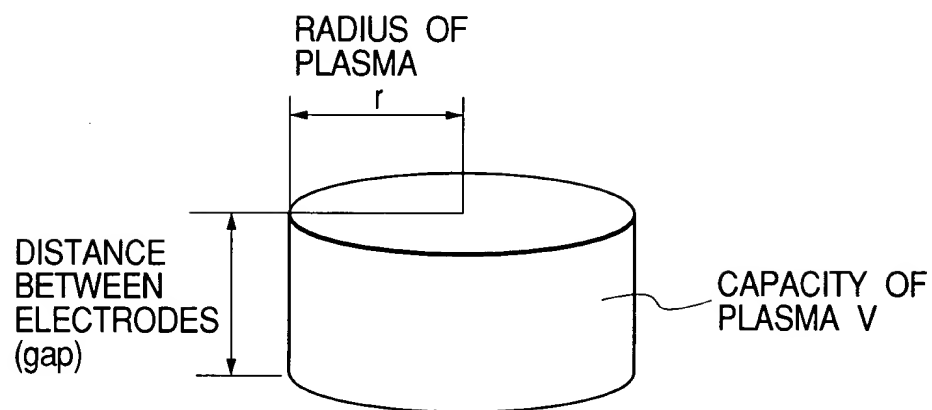
FIG. 44

[illegible]

FIG. 46



**FIG. 47**



**FIG. 48**

